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| 13. ABSTRACT (Maximum 200 words) Major accomplishments of this program are the demonstrations summarized below: (1) Large grain (0.5 to 0.8µm), high preferred orientation (100) films of Pt on SiO ₂ /Si substrates by use of high deposition temperatures (600-650°C) with a trace of reactive O ₂ gas in the rf-PM sputtering gas. The Pt film, besides functioning as metallization for bottom electrodes for capacitors, promotes epitaxial like growth within its large grains and high crystal quality of the overlying KTN film. (continued on reverse side) | | | | | |
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- (2) Epitaxial growth of KTN films on GaAs (100) and 'r' plane' (1012) Sapphire substrates with film normal along $\langle 100 \rangle$ polar direction.
- (3) First time observation of Ferroelectric Curie-Weiss behavior of KTN films by rf-PM sputtering on GaAs and Pt/SiO₂/Si substrates with peak dielectric constants of nearly 2250 (@ 1 KHz) ;Sharp Curie transition temperatures(-9 to +3°c) with bulk single crystal like characteristics.
- (4) High optical transmittivity of KTN films on Sapphire with nearly 99.5% of theoretical transmittivity.
- (5) High quadratic EO effect in paraelectric phase of KTN films on GaAs and Si substrates. Observed EO response is nearly 70% larger than for substrates.Observed EO effect is nearly 70% larger than for the same effect in PLZT thin films in ferroelectric phase.

F I N A L R E P O R T

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- NAME OF INSTITUTION: TRW Inc
- AUTHORS OF REPORT: Dr.Sanat Sashital
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DURING THIS REPORTING PERIOD, INCLUDING JOURNAL REFERENCES:
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S.Esener.Submitted to Applied Physics Letters.Dec,92.Anticipated publication
date: June 7,1993 ..Copies of this Ms have previously been mailed to
Drs.R.Guenther and M.Ciftan.
- SCIENTIFIC PERSONNEL SUPPORTED BY THIS PROJECT AND DEGREES AWARDED
DURING THIS REPORTING PERIOD: S.Sashital
A Ph.D.(Electrical & Computer Engineering) was awarded to S.Krishnakumar by
UC San Diego,Ca.(Thesis Advisor:Prof.S.Esener) Dept Of ECE.
S.Krishnakumar was not financially supported by this contract;However,in accord with
an arrangement by Dr.Andrew Yang DARPA,MTO,samples and data were made available toUCSD.
- REPORT OF INVENTIONS (BY TITLE ONLY):
None

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BRIEF OUTLINE OF RESEARCH FINDINGS

(Final Report)

In addition to reporting progress during the period Jan 1- May 31,1993 ,this final report also summarizes the major accomplishments of the program .During this reporting period,approximately three phone conversations were had with Dr.M.Ciftan (ARO) in regard to project performance and relevant administrative issues.

Optimization of KTN thin film Electrooptic (EO) and Ferroelectric (FE) properties continued during this period.Property Optimization was performed with respect to basic materials characteristics(film structure,composition/stoichiometry etc.) via film synthesis parameters; e.g. substrate temperature,deposition rate,sputtering target composition etc.) As described in earlier progress reports,the epitaxial like film structural quality was excellent and reproducible , as observed from the sharpness and singularity of the x-Ray Bragg reflection peaks i.e. { 100 } and higher orders only.However deficiency of 'K' in the KTN films continued to be a challenge.The deficiency of K originates from the lower sticking coefficient on the substrates (GaAs,Pt/SiO₂ ,Sapphire etc.) at the deposition temperatures used (600-650° C).A higher excess 'K' concentration (25-30 atom%) in the sputtering target with lower substrate temperatures and deposition rates is anticipated to yield stoichiometric films with good structural quality in future work.The primary effect of 'K' deficiency is thought to lower the peak dielectric constant of the Curie temperature curve (i.e. the dielectric constant versus temperature behavior) of the KTN film than is observed in bulk single crystals.Thus, for KTN films reported here a peak dielectric constant of nearly 2250 is seen for a composition of K_{0.94}Ta_{0.62}Nb_{0.37}O₃ as compared to a peak value in excess of 20000 for bulk crystals of the same composition.The superior crystal structural quality of the films is reflected in the single crystal like sharpness of the Curie temperature plot.

Since a fundamental objective of this program was to demonstrate EO effects in KTN films (for application to various EO devices/systems of DoD's interest ; e.g. EO light modulators,active and passive waveguides,smart pixels etc.) ,attention was primarily focussed during this reporting period on the measurement of EO and optical properties of films .

Figure 1 shows the measured refractive index 'n' versus wavelength 'λ' of a KTN film (1.8 μm thick) on a Si substrate.As can be seen ,the variation is qualitatively that of bulk single crystals.However ,the 'n' measured at 6138 Å is lower than that observed in bulk single crystals (n=2.3). Similar behavior has been reported in other ferroelectric films (e.g. PLZT) also and is thought to arise from the 'K' or 'A' site cation deficiency in ABO₃ perovskite structure compounds.

EO coefficient measurements were made on KTN films deposited on Si and GaAs substrates. Sputtered Pt film electrodes were applied to yield transverse EO modulators i.e. E fields in film plane and optical field normal to the film. Using standard 'Lock-in' techniques, beam splitters, etc. the field induced refractive index change due to applied electric field was studied at room temperature as a measure of the EO effect. For purposes of comparison, a PLZT(61/29) film on a Pt film substrate (synthesized by Prof. Esener and his group at UCSD) was also similarly studied. Figure 2. clearly shows a substantially higher quadratic EO effect in KTN films (nearly 70% higher for KTN/Si than in PLZT films). It is noteworthy that the observed quadratic EO effect in the paraelectric phase of KTN at room temperature is higher than the quadratic EO effect in ferroelectric PLZT (Curie Temperature > 50°C). Since the nonlinear EO effect in the FE phase is usually an order of magnitude or higher than in the paraelectric phase, a substantially high value of EO coefficient may be expected for FE KTN films. **This observation of EO effect is the first report of such measurements in KTN films.** The differences in the EO response in films on GaAs and Si are thought to arise from the slight differences in crystallinity and composition. Thus, KTN films offer themselves as strong candidates for further studies, EO property maximization via improved materials characteristics and several important devices/systems for military and commercial application.

Major accomplishments of this program are the demonstrations summarized below:

- (1) Large grain (0.5 to 0.8 μm), high preferred orientation (100) films of Pt on SiO_2/Si substrates by use of high deposition temperatures (600-650°C) with a trace of reactive O_2 gas in the rf-PM sputtering gas. The Pt film, besides functioning as metallization for bottom electrodes for capacitors, promotes epitaxial like growth within its large grains and high crystal quality of the overlying KTN film.
- (2) Epitaxial growth of KTN films on GaAs (100) and 'r' plane' (1012) Sapphire substrates with film normal along $\langle 100 \rangle$ polar direction.
- (3) First time observation of Ferroelectric Curie-Weiss behavior of KTN films by rf-PM sputtering on GaAs and $\text{Pt}/\text{SiO}_2/\text{Si}$ substrates with peak dielectric constants of nearly 2250 (@ 1 KHz); Sharp Curie transition temperatures (-9 to +3°C) with bulk single crystal like characteristics.

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- (5) High quadratic EO effect in paraelectric phase of KTN films on GaAs and Si substrates. Observed EO response is nearly 70% larger than for substrates. Observed EO effect is nearly 70% larger than for the same effect in PLZT thin films in ferroelectric phase.

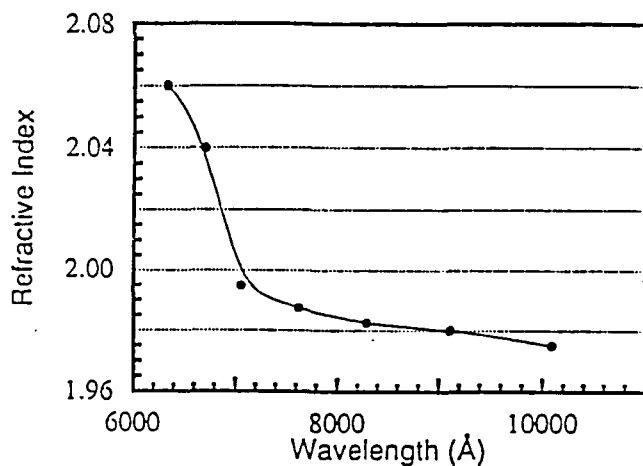


Figure 1. Refractive index vs. Wavelength KTN film on Si substrate.

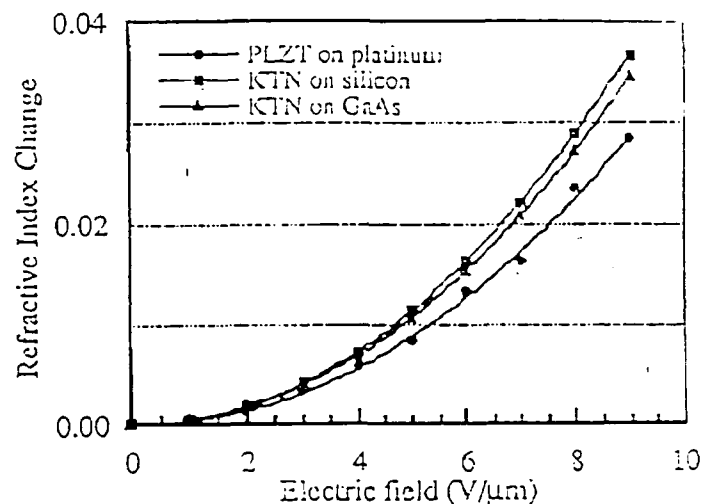


Figure 2. EO effect in KTN film on GaAs, Si substrates. PLZT film on Pt/Si substrate shown for comparison

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